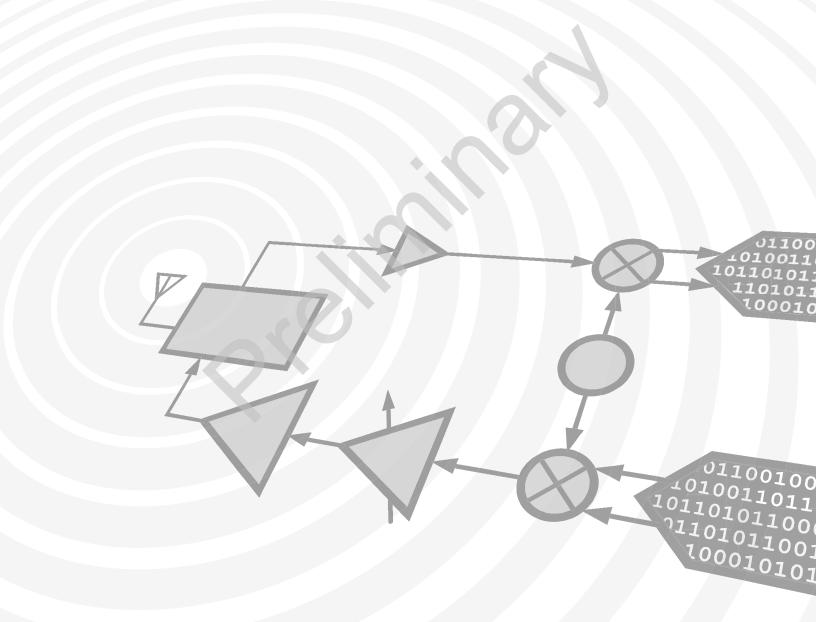




Analog Devices Welcomes Hittite Microwave Corporation



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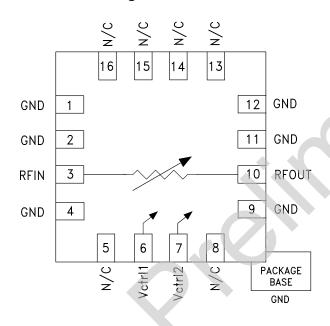
GaAs MMIC VOLTAGE-VARIABLE ATTENUATOR, 5 - 26.5 GHz

Typical Applications

The HMC712ALP3CE is ideal for:

- Point-to-Point Radio
- VSAT Radio
- Test Instrumentation
- Microwave Sensors
- Military, ECM & Radar

Functional Diagram



Features

Wide Bandwidth: 5 - 26.5 GHz

Excellent Linearity: +28 dBm Input P1dB

Wide Attenuation Range: 28 dB

Absorptive Topology

Singe or Dual Control Operation

16 Lead 3x3mm SMT Package: 9mm²

General Description

The HMC712ALP3CE is an absorptive Voltage Variable Attenuator (VVA) which operates from 5 - 26.5 GHz and is ideal in designs where an analog DC control signal must be used to control RF signal levels over a 28 dB amplitude range. It features two shunt-type attenuators which are controlled by two analog voltages, Vctrl1 and Vctrl2. Optimum linearity performance of the attenuator is achieved by first varying Vctrl1 of the 1st attenuation stage from -3V to 0V with Vctrl2 fixed at -3V. The control voltage of the 2nd attenuation stage, Vctrl2, should then be varied from -3V to 0V, with Vctrl1 fixed at 0V. The HMC712ALP3CE is housed **RoHS** in compliant 3x3 mm QFN leadless package

However, if the Vctrl1 and Vctrl2 pins are connected together it is possible to achieve the full analog attenuation range with only a small degradation in input IP3 performance. Applications include AGC circuits and temperature compensation of multiple gain stages in microwave point-to-point and VSAT radios.

Electrical Specifications, $T_A = +25^{\circ}$ C, 50 Ohm system

Parameter		Тур.	Max.	Units
5 - 16 GHz Insertion Loss 16 - 24 GHz 24 - 26.5 GHz		3.5 4.5 5.5		dB dB dB
Attenuation Range		28		dB
Input Return Loss		12		dB
Output Return Loss		10		dB
Input Power for 1 dB Compression (any attenuation)		28		dBm
Input Third Order Intercept (Two-tone Input Power = 10 dBm Each Tone)		32		dBm



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GaAs MMIC VOLTAGE-VARIABLE ATTENUATOR, 5 - 26.5 GHz

Absolute Maximum Ratings

RF Input Power	+30 dBm	
Control Voltage Range	+1 to -5V	
Channel Temperature	150 °C	
Continuous Pdiss (T = 85 °C)	1W	
Thermal Resistance (Channel to ground paddle)	66 °C/W	
Storage Temperature	-65 to +150 °C	
Operating Temperature	-40 to +85 °C	
ESD Sensitivity (HBM)	Class 1A	

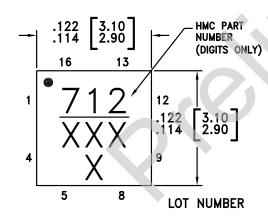
Control Voltages

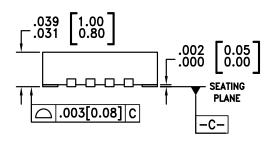
Vctrl1	-3 to 0V @ 10 μA
Vctrl2	-3 to 0V @ 10 μA



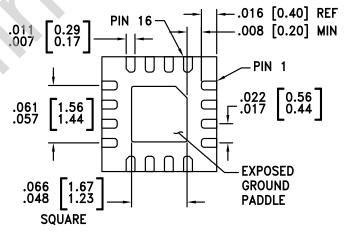
ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

Outline Drawing





BOTTOM VIEW



NOTES:

- PACKAGE BODY MATERIAL: LOW STRESS INJECTION MOLDED PLASTIC SILICA AND SILICON IMPREGNATED.
- 2. LEAD AND GROUND PADDLE MATERIAL: COPPER ALLOY.
- 3. LEAD AND GROUND PADDLE PLATING: 100% MATTE TIN.
- 4. DIMENSIONS ARE IN INCHES [MILLIMETERS].
- 5. LEAD SPACING TOLERANCE IS NON-CUMULATIVE.
- PAD BURR LENGTH SHALL BE 0.15mm MAX.PAD BURR HEIGHT SHALL BE 0.05mm MAX.
- 7. PACKAGE WARP SHALL NOT EXCEED 0.05mm
- 8. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.
- 9. REFER TO HITTITE APPLICATION NOTE FOR SUGGESTED PCB LAND PATTERN.